

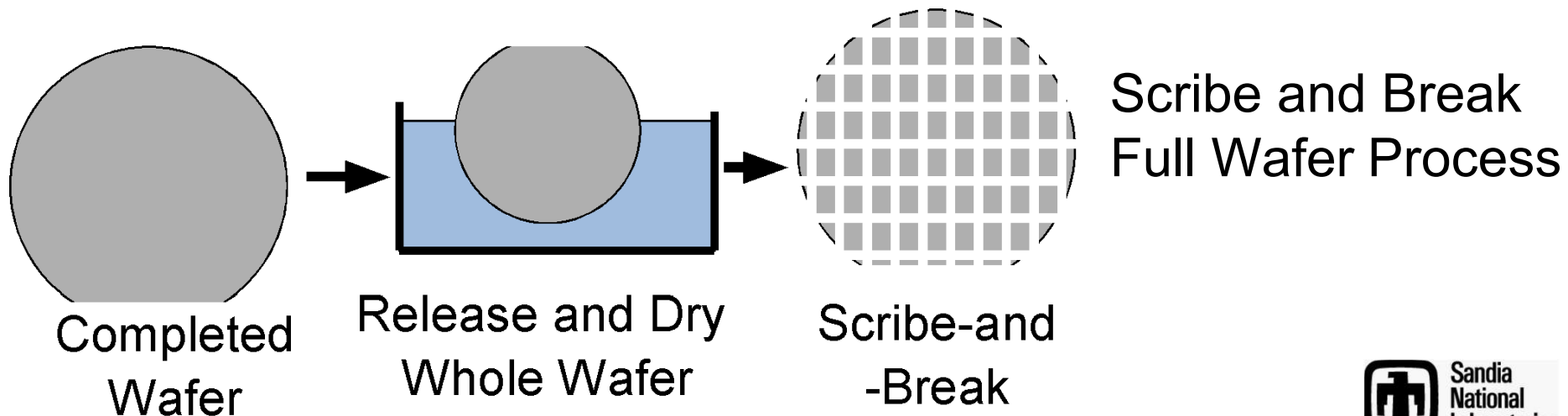
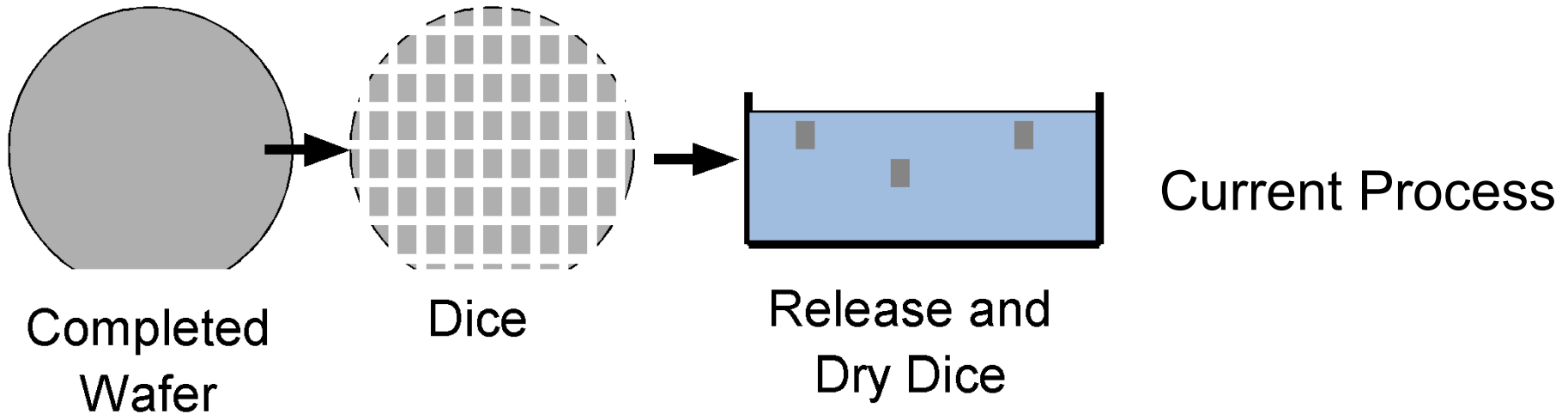
SCRIBE-AND-BREAK FOR POST RELEASE MEMS DIE SEPARATION

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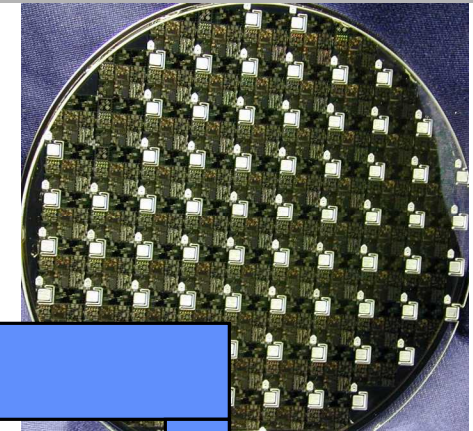
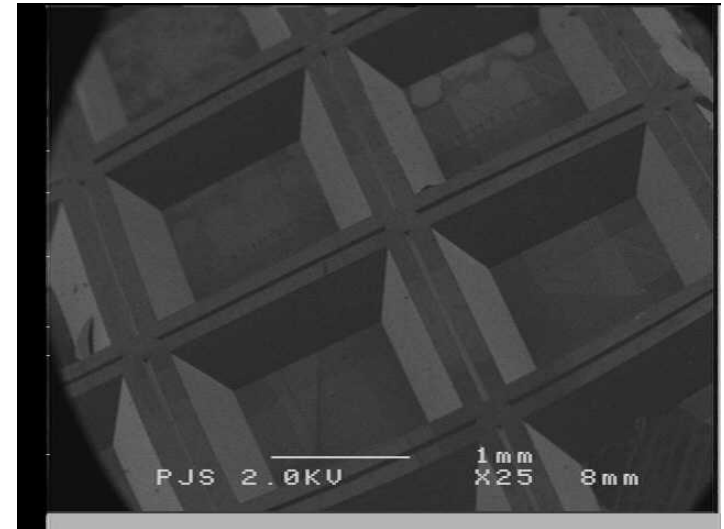
505 845-7931

WHY POST RELEASE DIE SINGULATION FOR SURFACE MICROMACHINES?



APPROACHES

- Dice and then Release
 - Sandia
 - No process changes
- Permanent Cap
 - Motorola
 - Provides first level package but it changes the device and the process
- Temporary Cap
 - Analog Devices
 - Need to allocate real estate for the cap
 - Changes the Process
- Break after Release
 - Texas Instruments



blue mounting tape

wafer



CRITERIA AND CHOICES

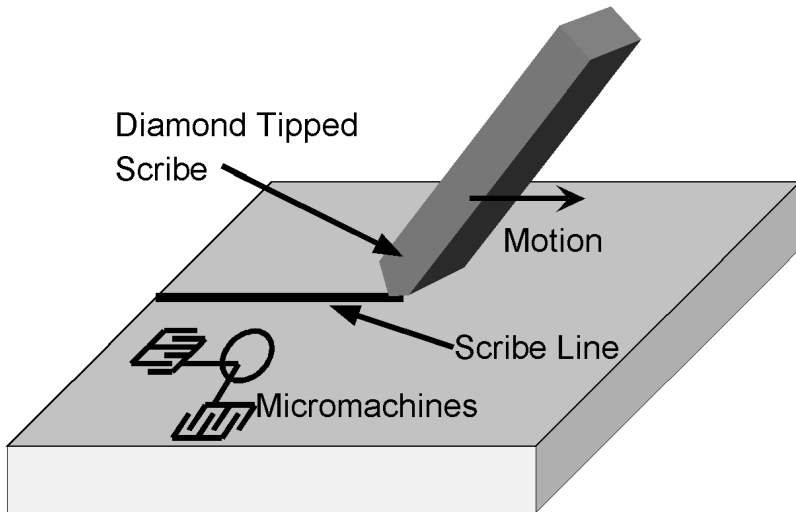
- **Process must be**
 - Dry
 - Particle free
 - Robust
- **Alternatives**
 - Analog Devices
 - Texas Instruments (partial saw and break)
 - Laser Cutting
 - Laser Scribing
 - Diamond Scribing



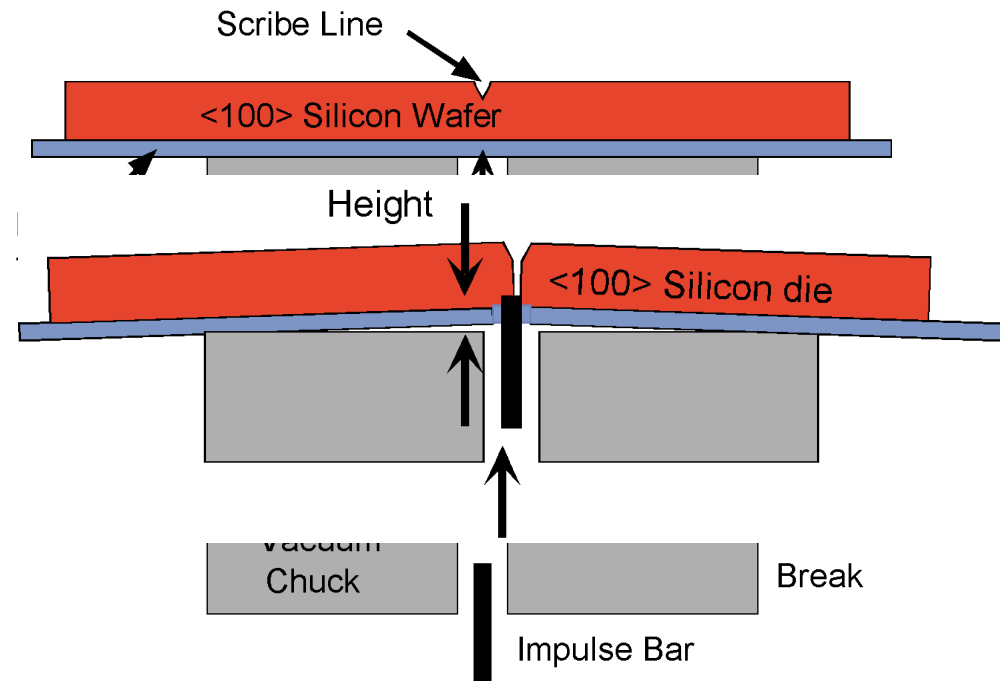
ADVANTAGES TO SCRIBE AND BREAK

- **No process changes**
- **100% of die size devoted to MEMS**
- **Transparent to designers**
- **Fast**
- **Low cost**
- **Disadvantage**
 - **Not well understood**

SCRIBE AND BREAK



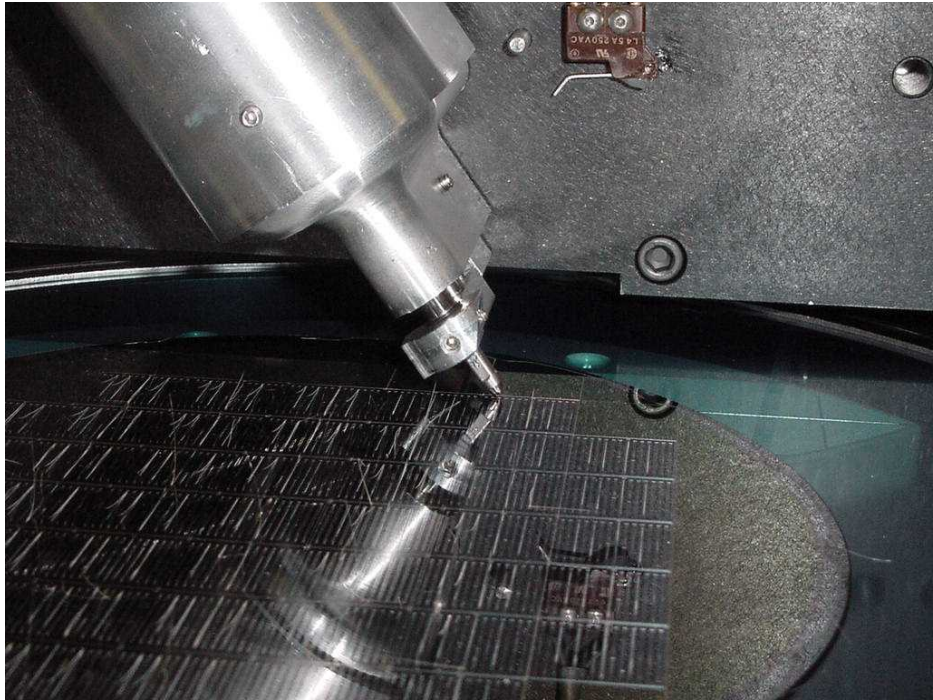
1. Released MEMS wafer is scored with a diamond scribe



2. Wafer is broken into die along scribe line

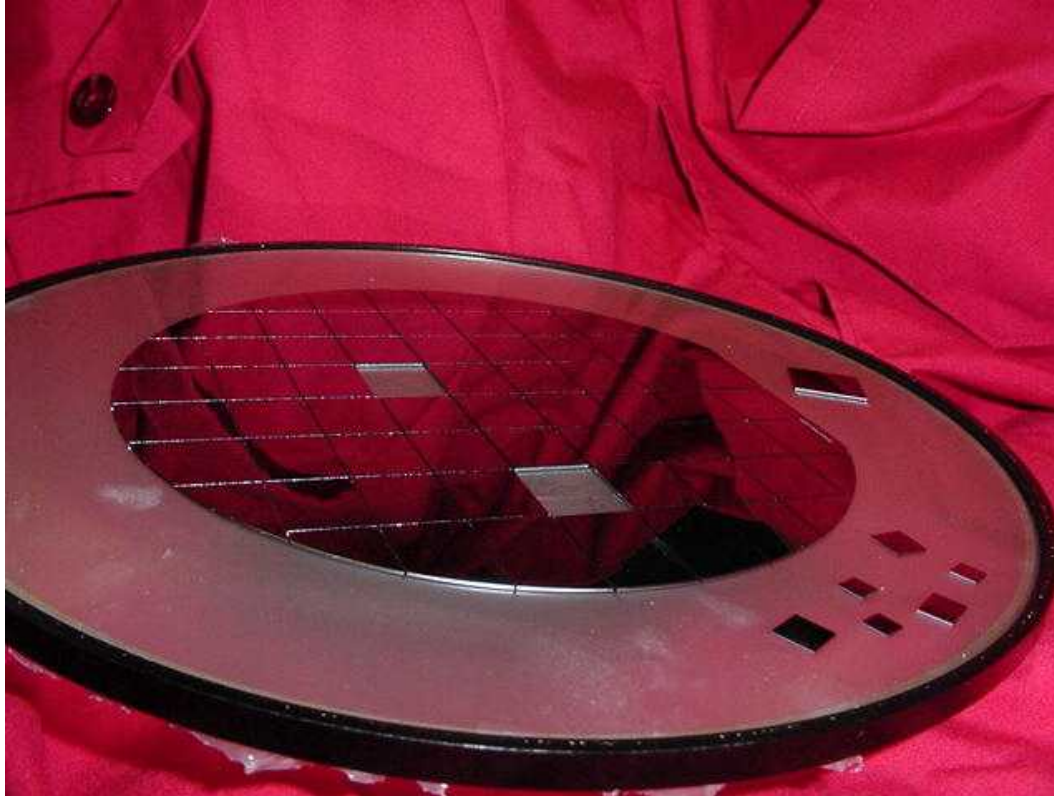
Post release die singulation enables full wafer release of MEMS devices

SCRIBE AND BREAK MACHINE



- **GST Scriber/Breaker**
- **Manufactured by Dynatex International, Santa Rosa, California**
- **Handles substrates up to 150 mm in diameter**

WAFERS MOUNTING



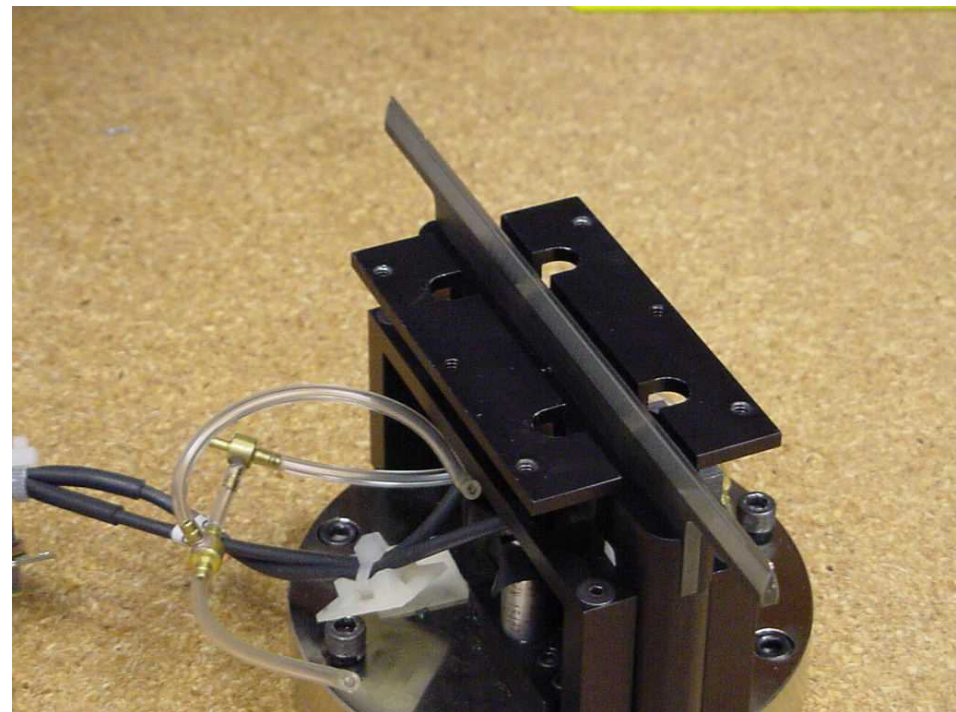
- Wafers mounted on frame before scribing (either standard or UV tape)



VACUUM CHUCK AND BREAKER



• **Vacuum chuck**

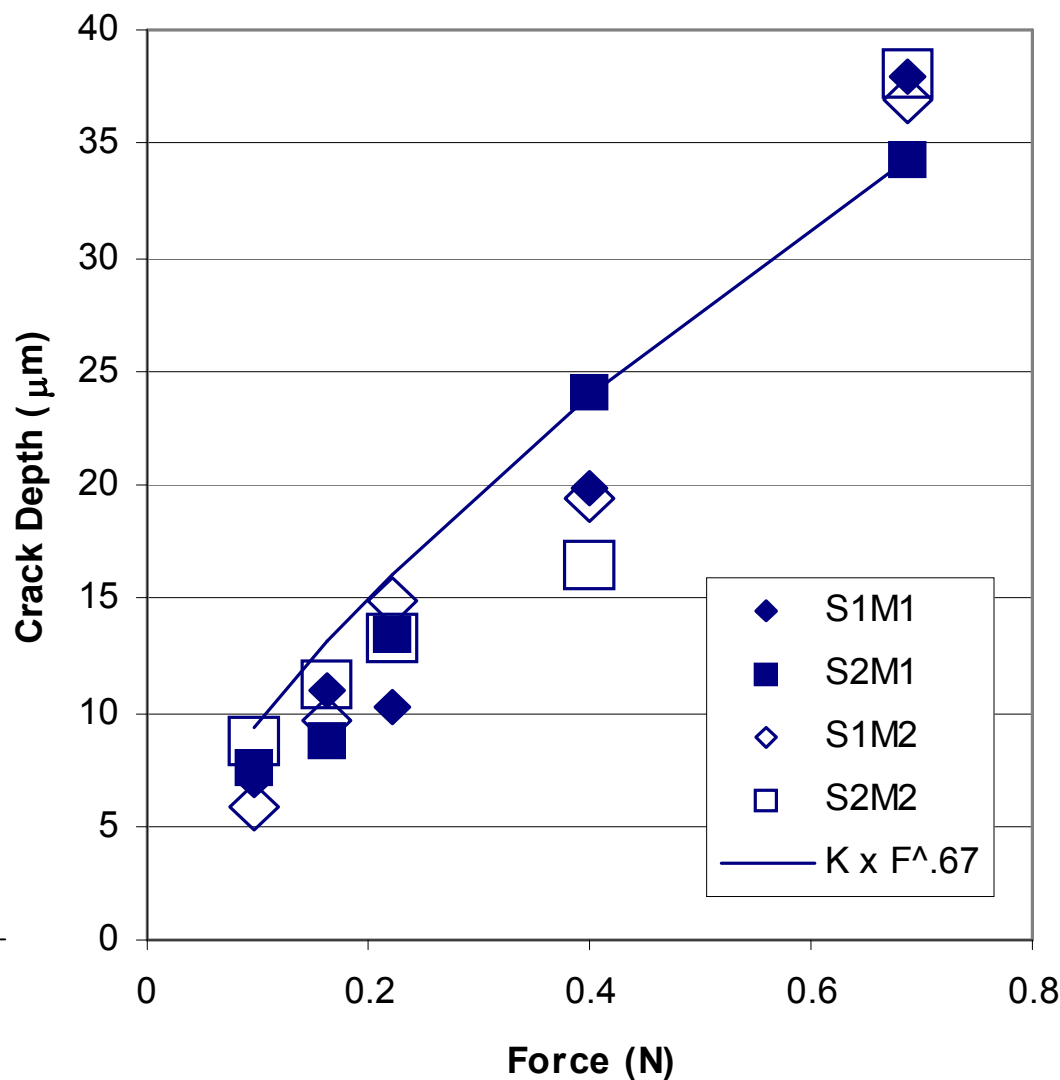


Breaking bar

MEDIAN CRACK DEPTH

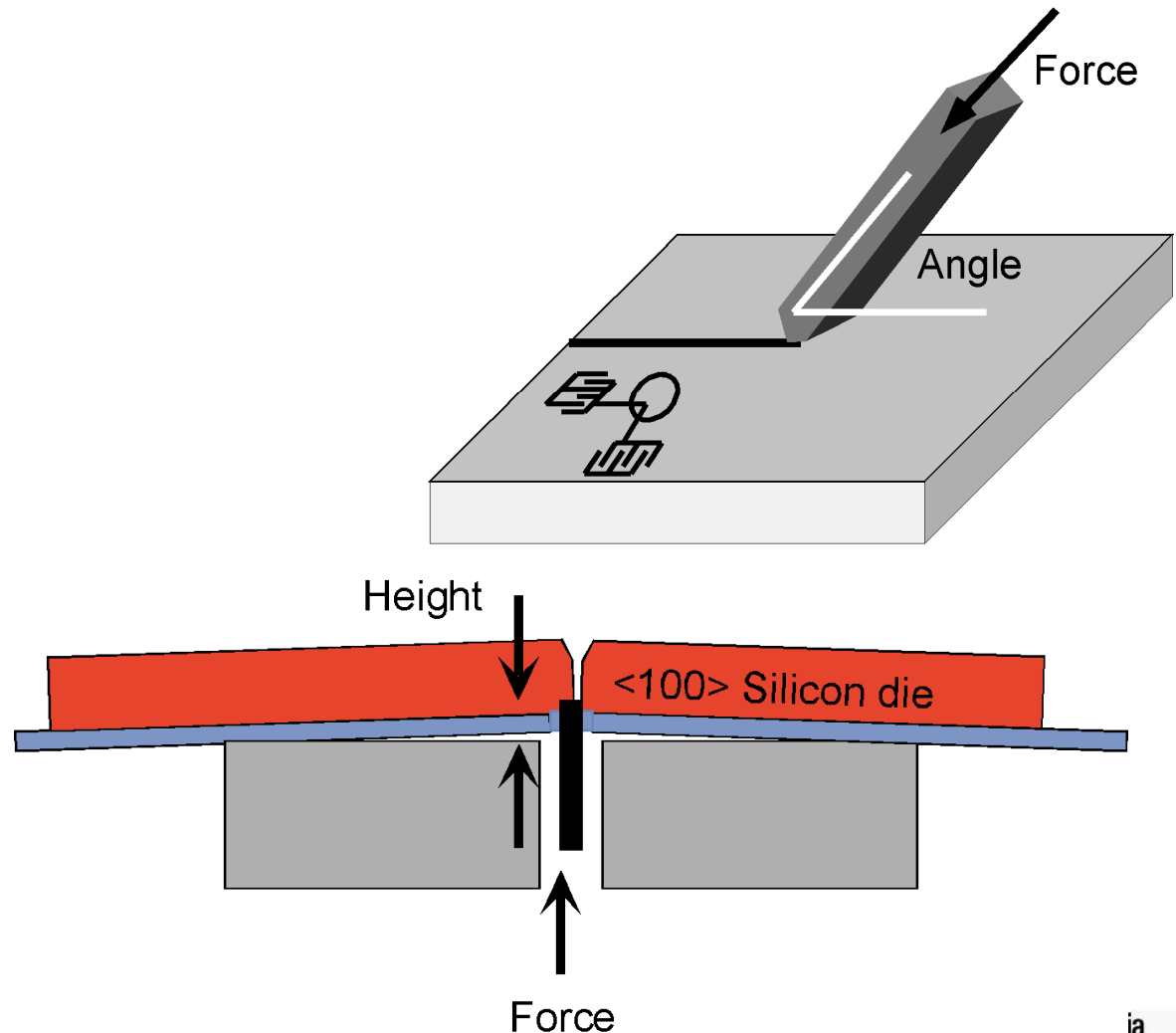
- Measurements were taken with 2 different SEMs on two different samples
- 4 samples total

$$depth = \frac{\left(\frac{2CF}{K_{IC}} \right)^{2/3}}{\pi}$$



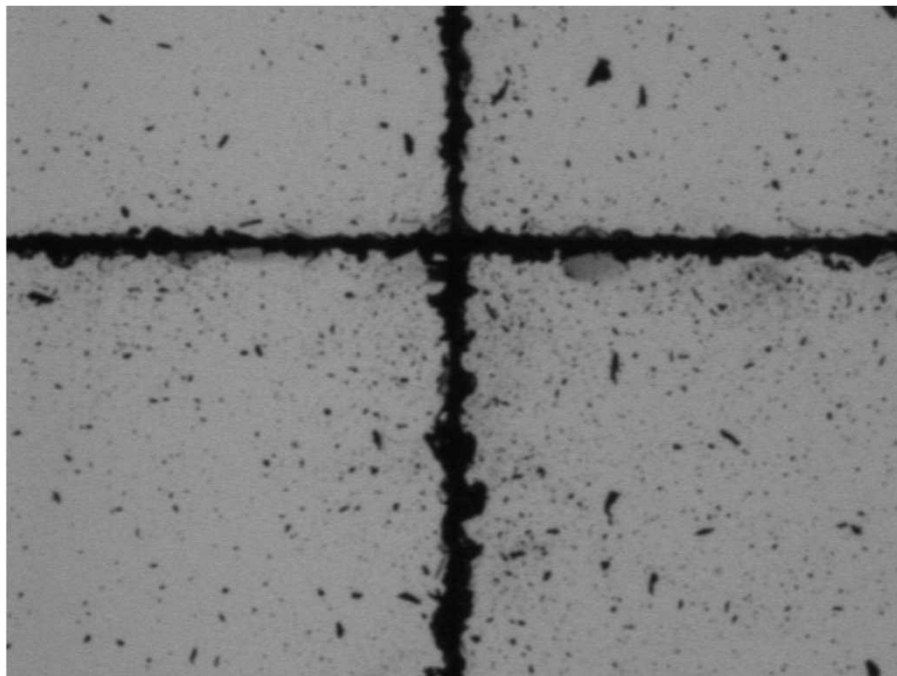
DESIGN OF EXPERIMENTS TO FIND PARAMETER IMPORTANCE

- Machine has 13 parameters
- 4 parameter full factorial
- Run 3 times in different orders
- Parameters used were scribe force, scribe angle, break pressure, and break height

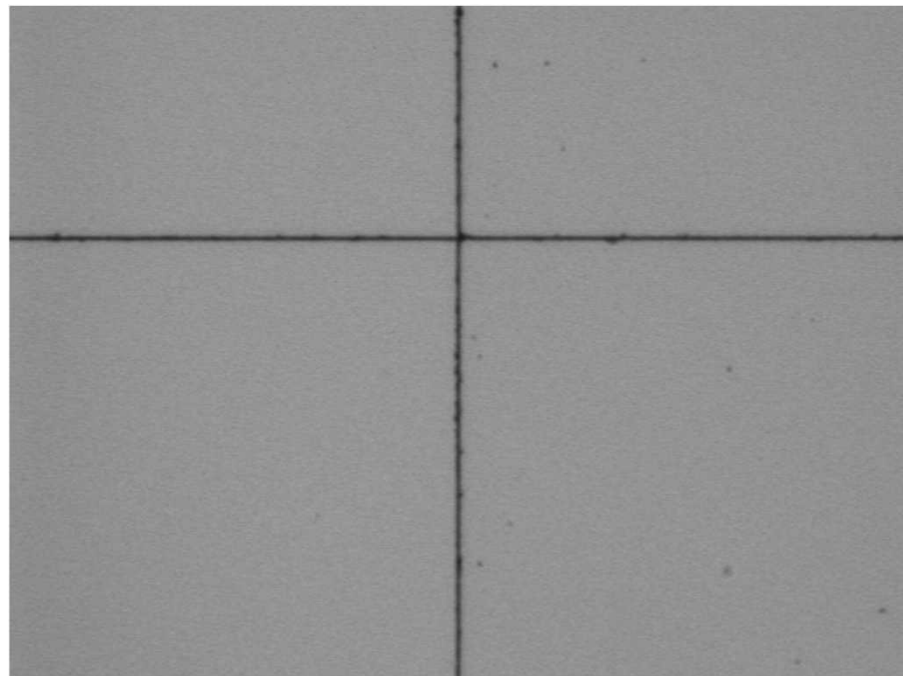




TO QUANTIFY SCRIBE QUALITY

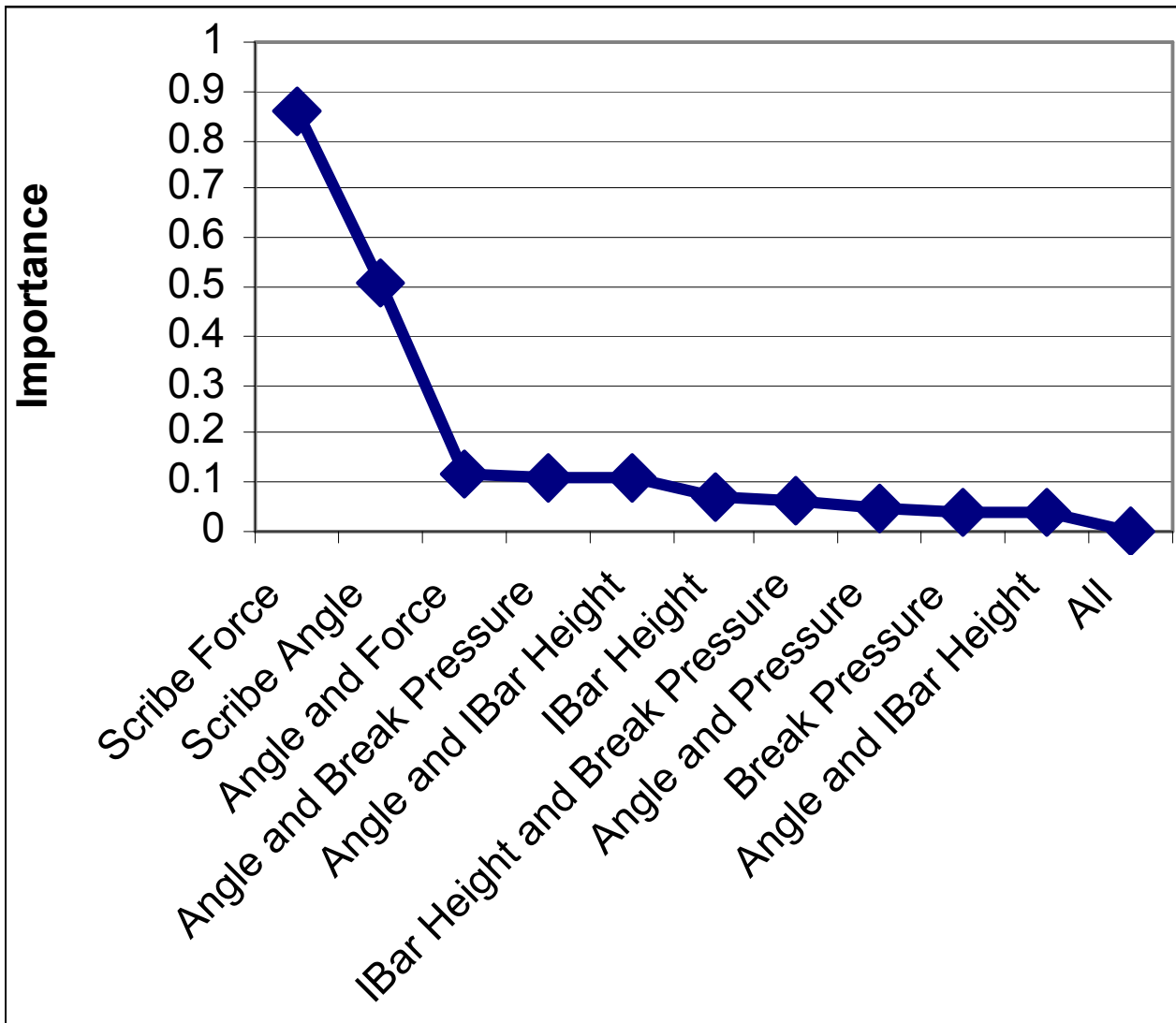


Quality 5 scribe

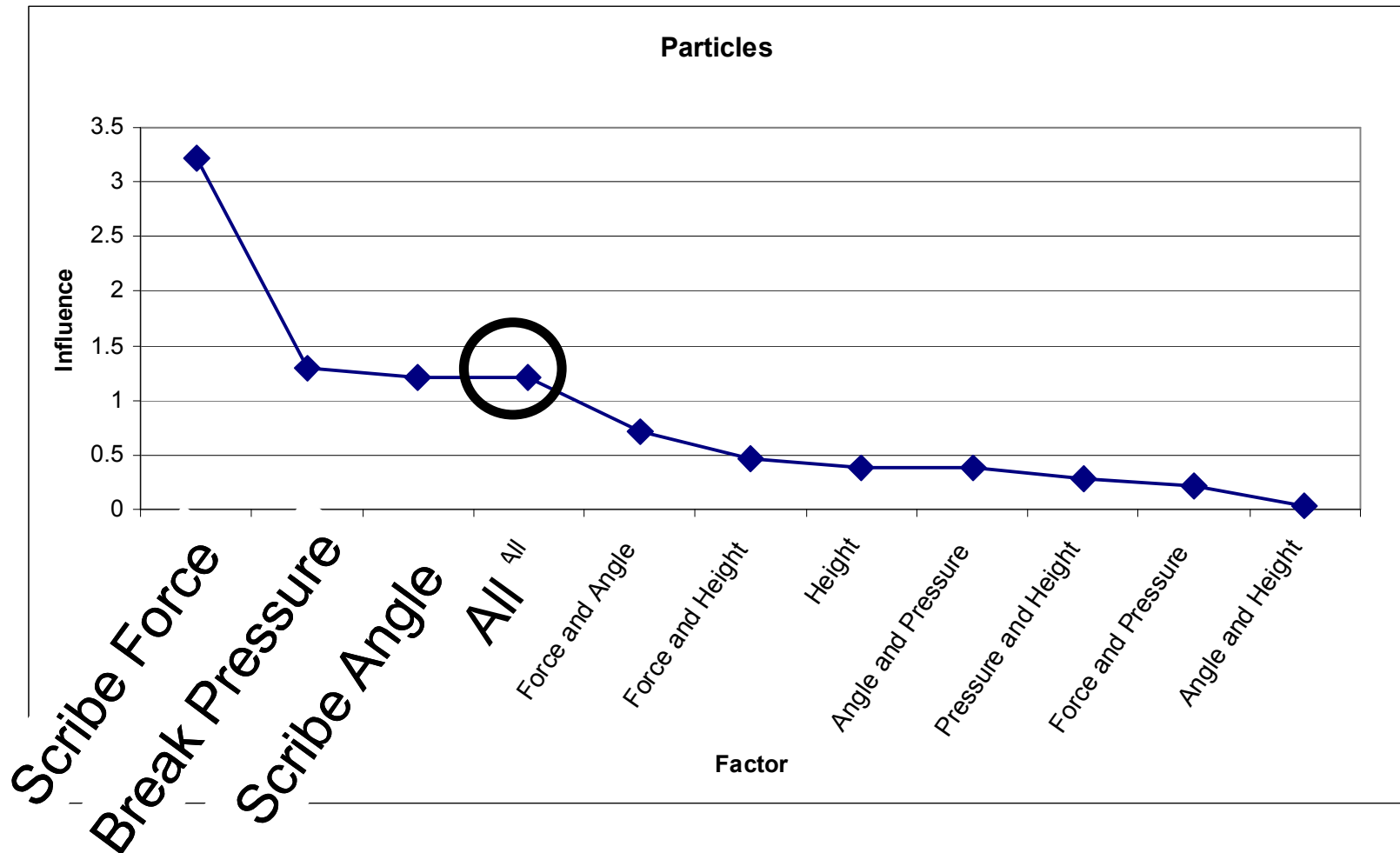


Quality 1 scribe

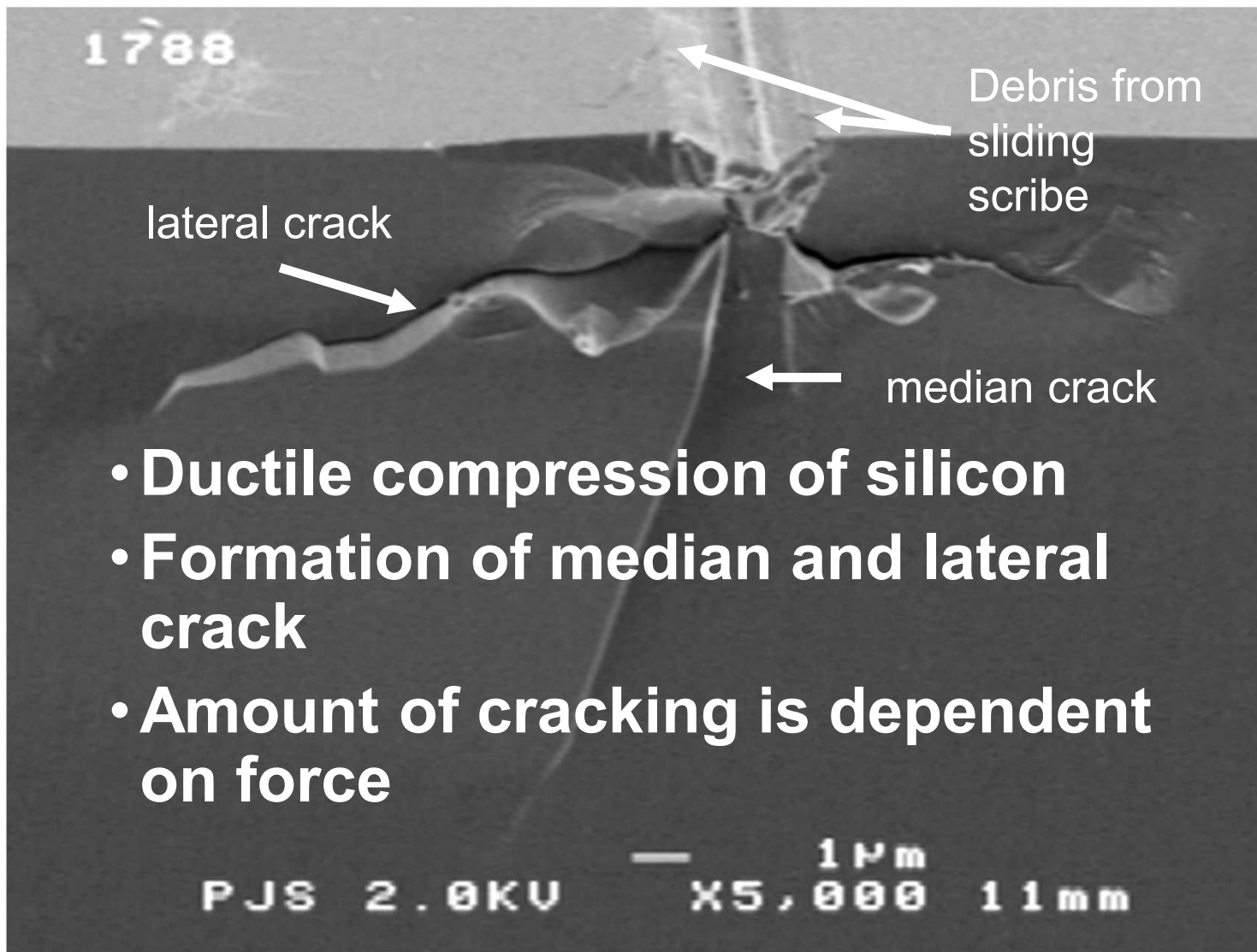
DESIGN OF EXPERIMENTS QUALITY



DESIGN OF EXPERIMENTS-PARTICLES



WHAT IS GOING ON DURING SCRIBING?



- Ductile compression of silicon
- Formation of median and lateral crack
- Amount of cracking is dependent on force



WHAT IS GOING ON DURING SCRIBING?

- **Diamond tip creates a median crack underneath the scribe line**

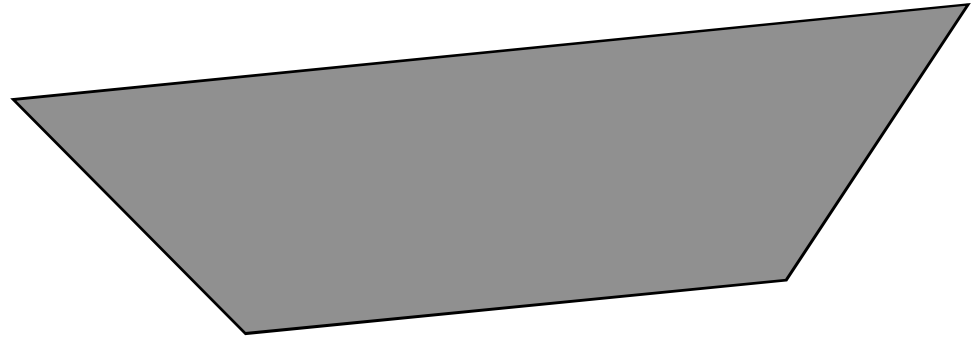
$$K = \sqrt{\frac{\textit{crack_depth}}{2 \cdot \textit{crack_radius}}}$$

- **This creates a stress concentration at the crack tip**
- **At the tip, the crack radius is about 2 A**
- **For a 20 um deep crack, this gives a stress concentration factor of 223**

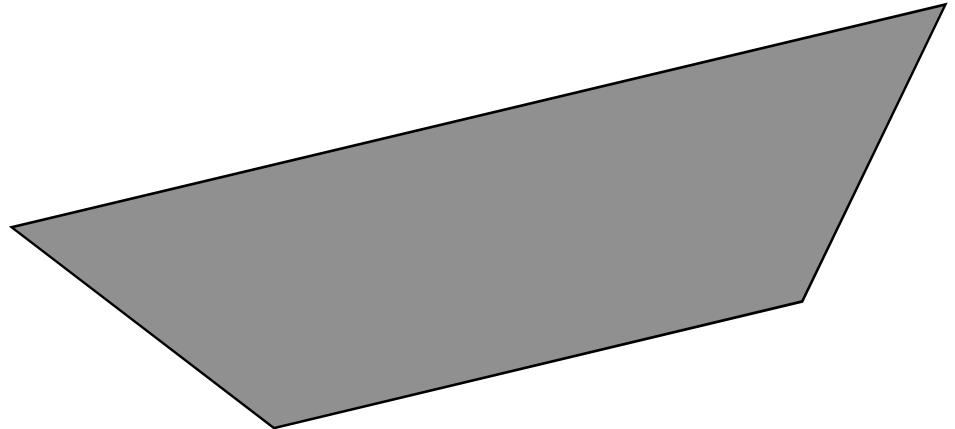


INFLUENCE OF SCRIBE ANGLE

- **Shallow Angle**



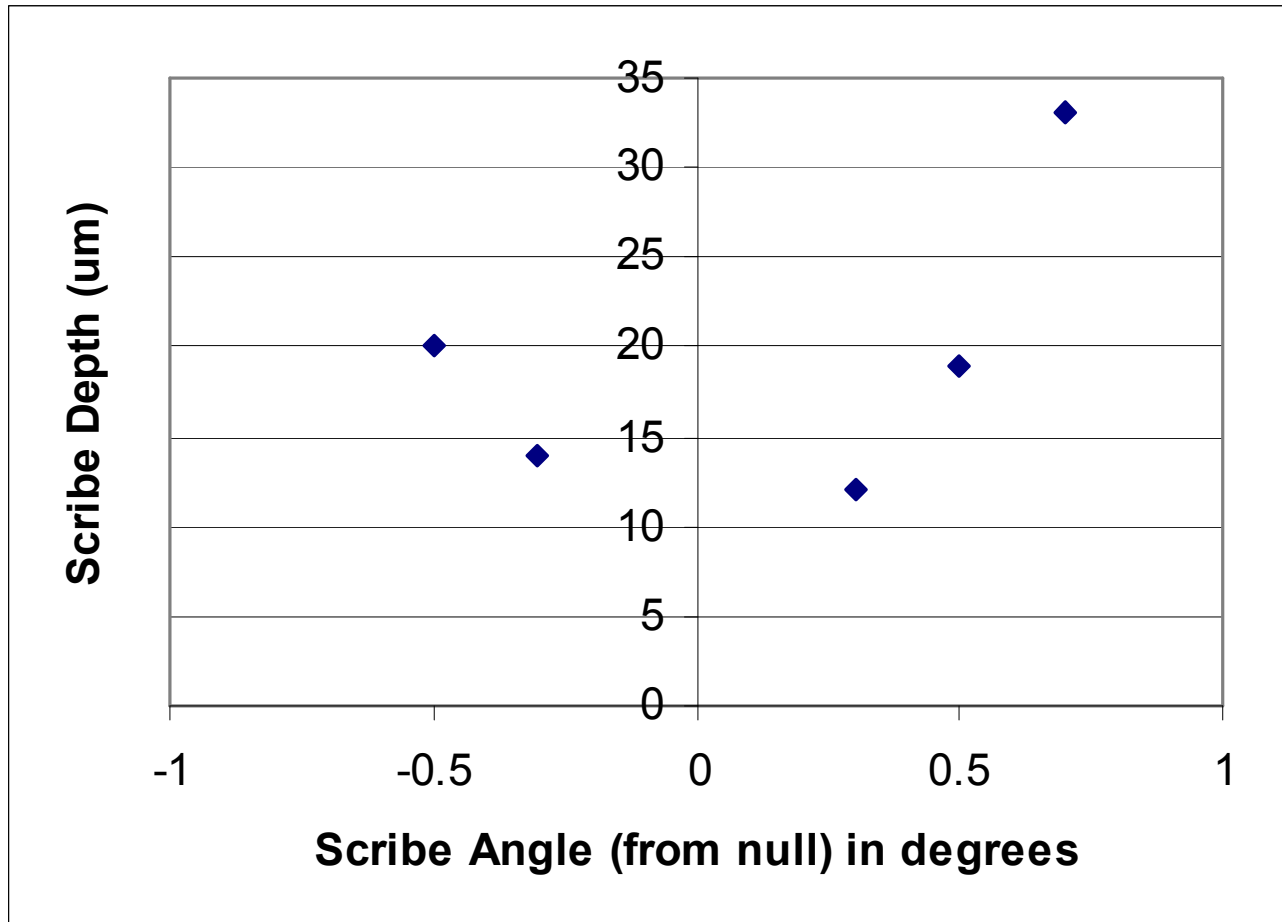
- **Sharp Angle**



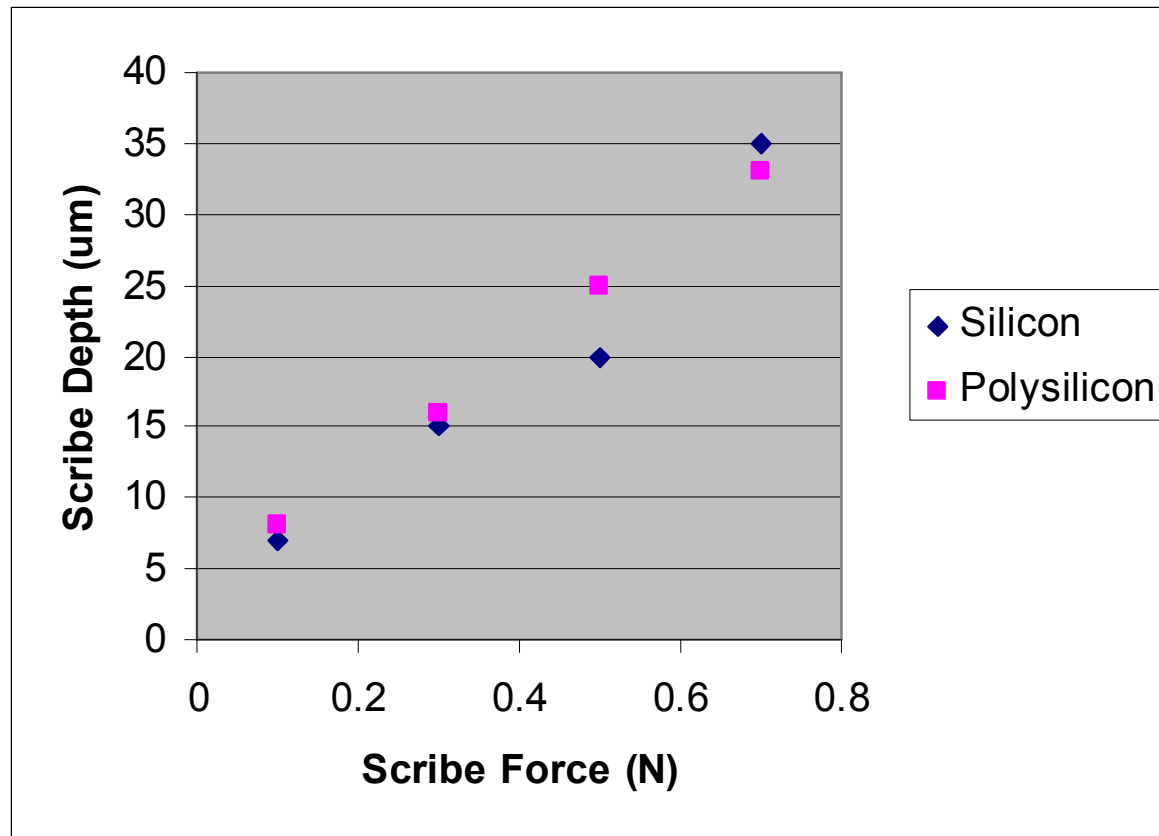
- **The sharper the angle the more material is displaced**



SCRIBE DEPTH VS SCRIBE ANGLE

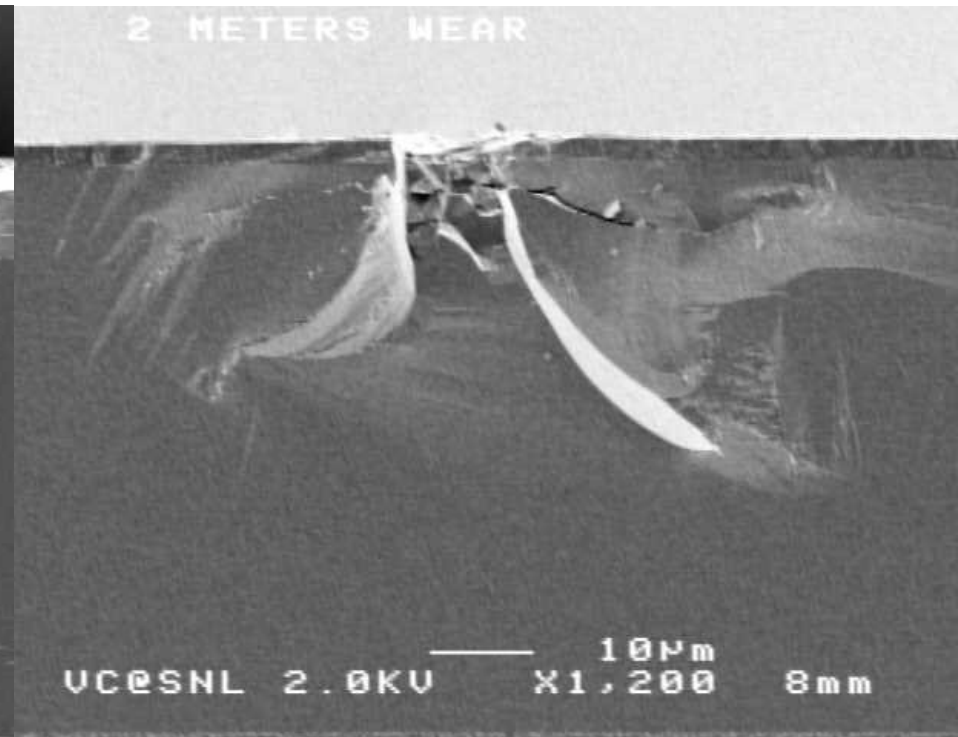
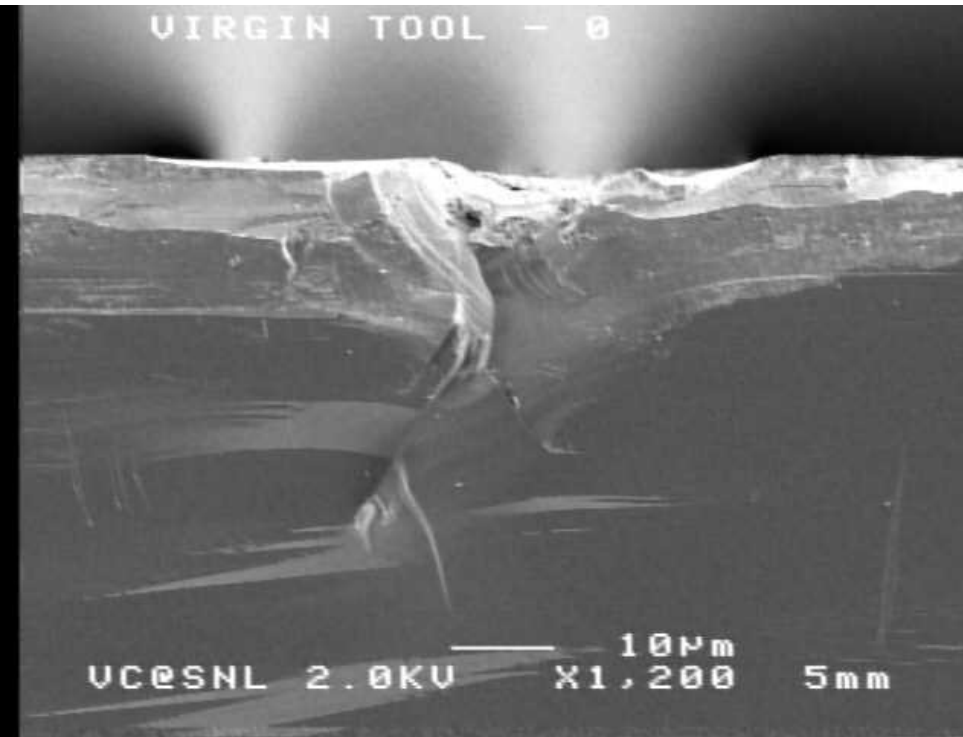


SCRIBING POLYSILICON VS SILICON



- The two films are roughly equivalent in terms of scribe performance

TUNGSTEN FILMS IN STREETS



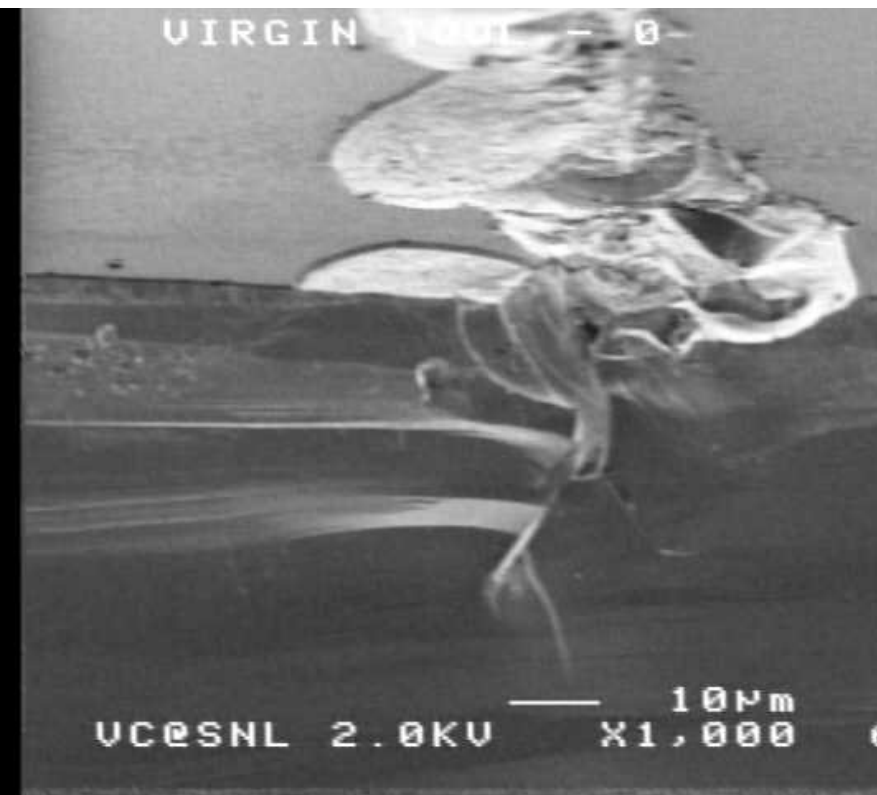
Initial

2 meters of wear

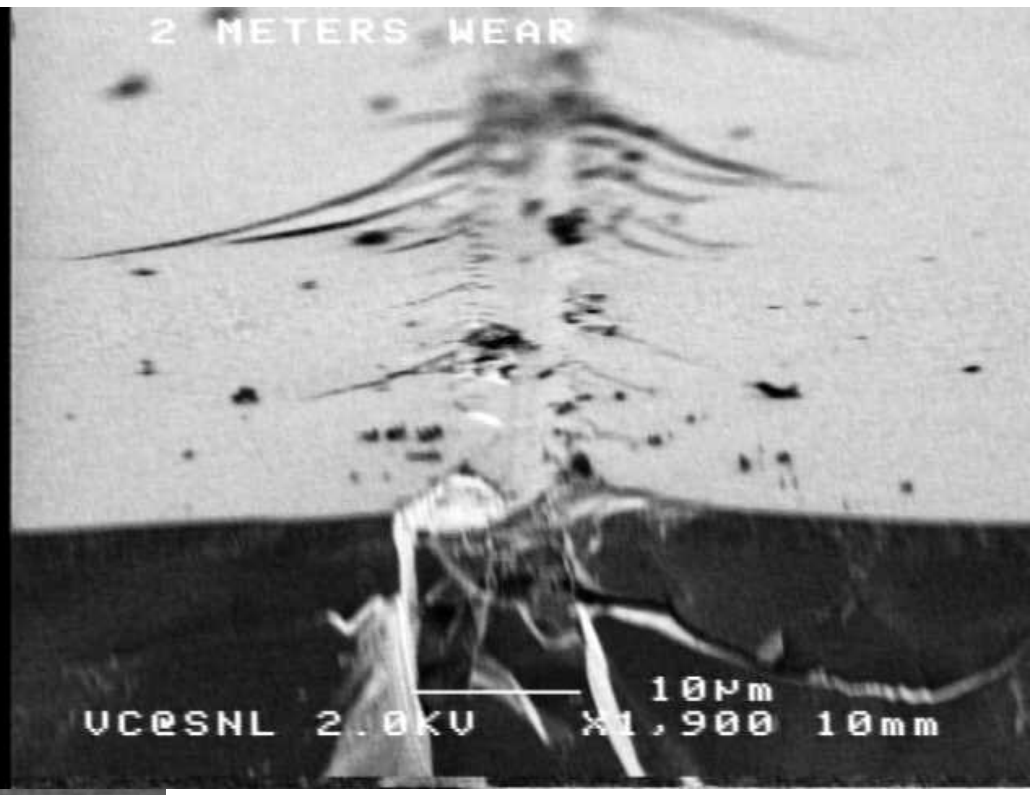
Tungsten thin film on silicon



TUNGSTEN FILMS IN STREETS

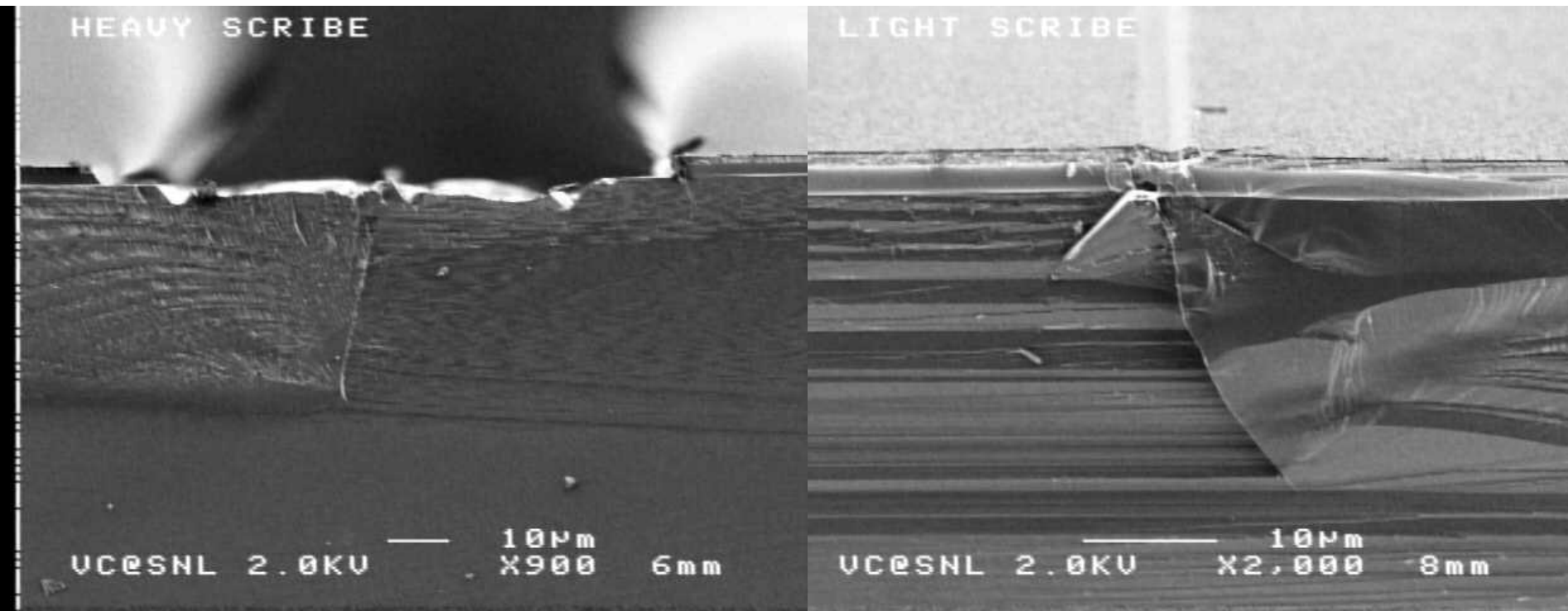


Initial



2 meters of wear

WEAR FROM Si_3N_4



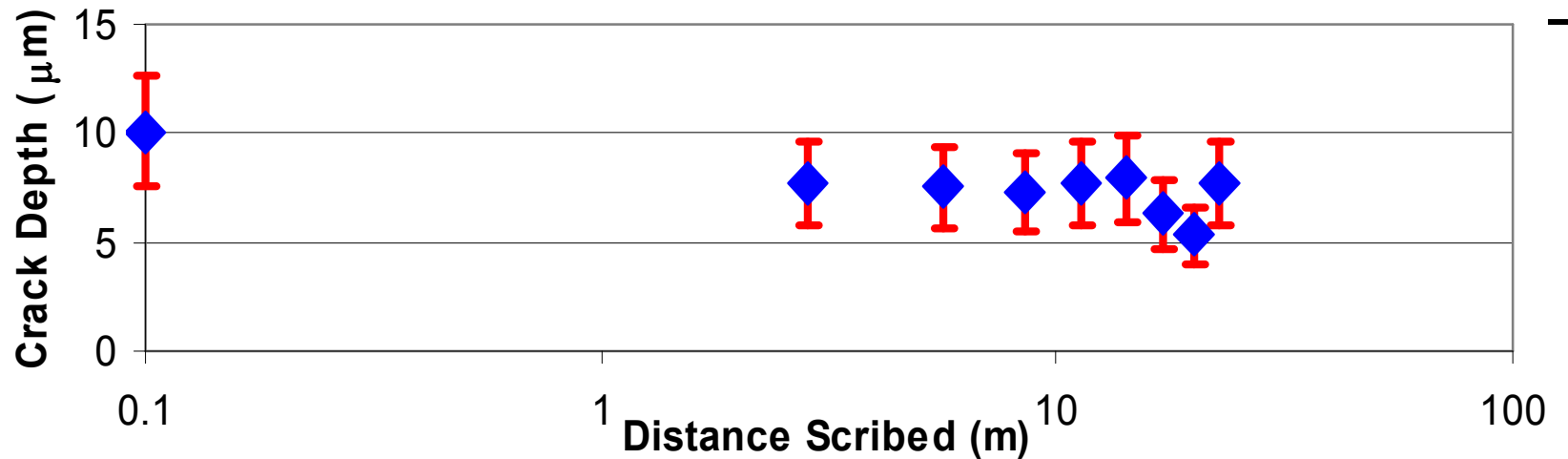
virgin scribe

After 1 meter of wear
(7 passes across the
wafer

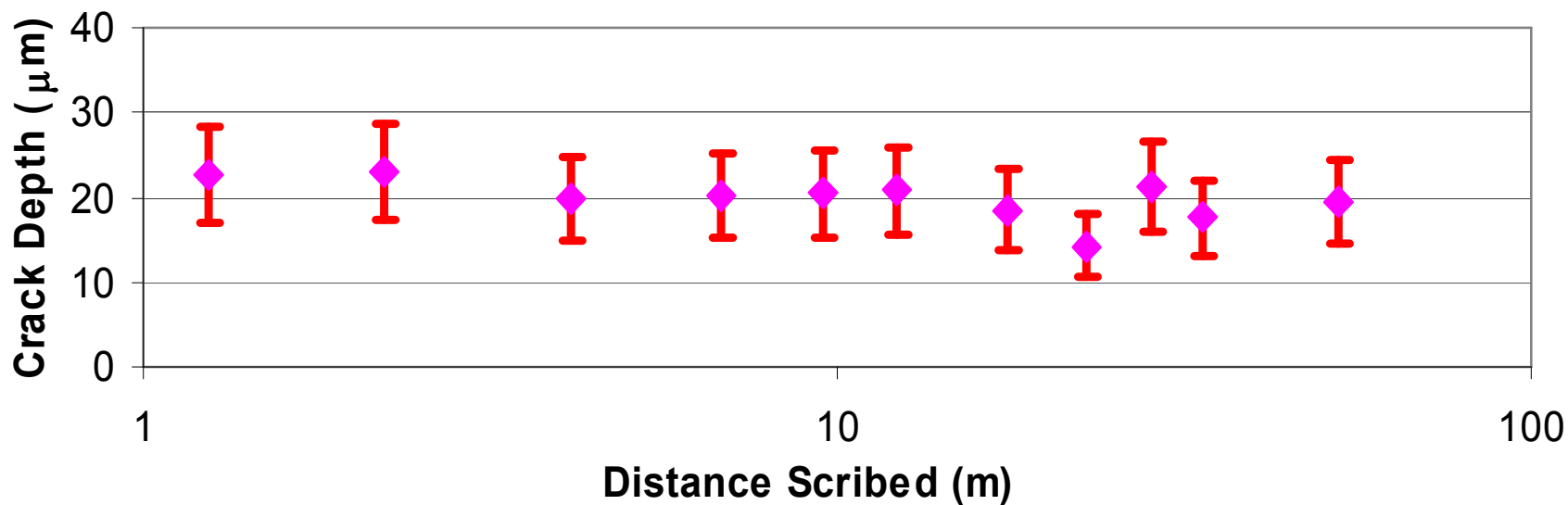


WEAR IN SCRIBE TIP ON SILICON

Minimal Scribe Force



High Scribe Force



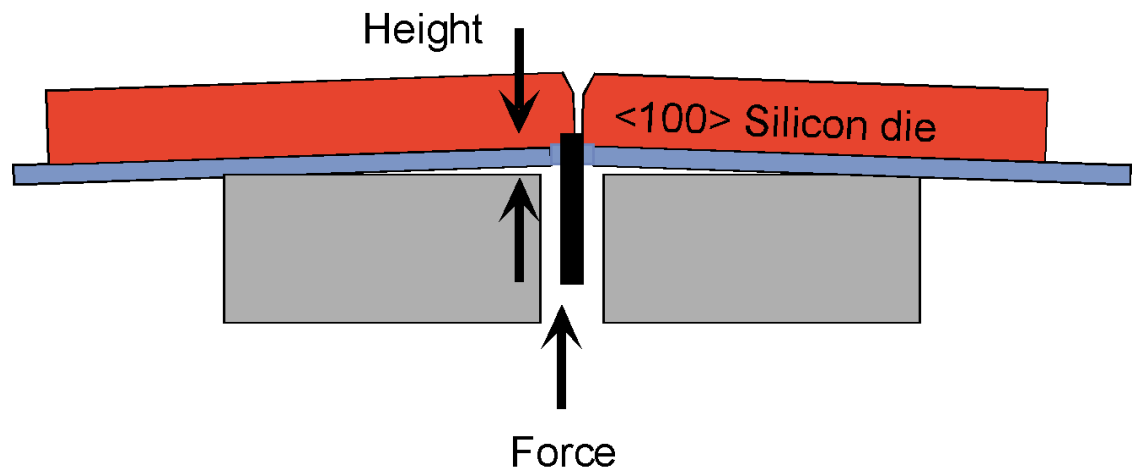


UNANSWERED QUESTION - WEAR

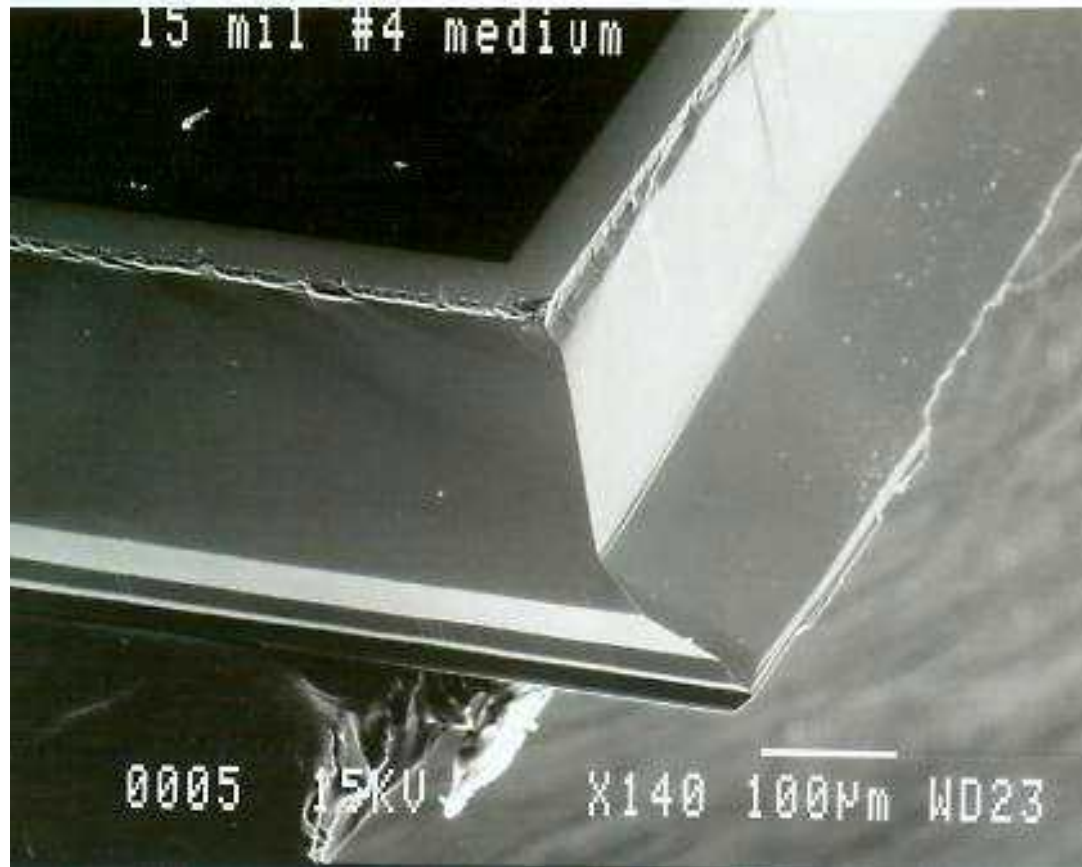
- **The vendor recommends that the scribe tip be replaced when the wafers stop breaking or when the scribe line becomes faint**
- **Wear in the scribe tip is one source of inconsistency in an otherwise consistent process**

WHAT IS GOING ON DURING BREAKING?

- The wafer can be modeled as a simply supported plate
- The impulse bar can be modeled as an impulse function to the silicon wafer
- If the applied stress is high enough, the wafer cracks along the scribe line



CANTILEVER CURL

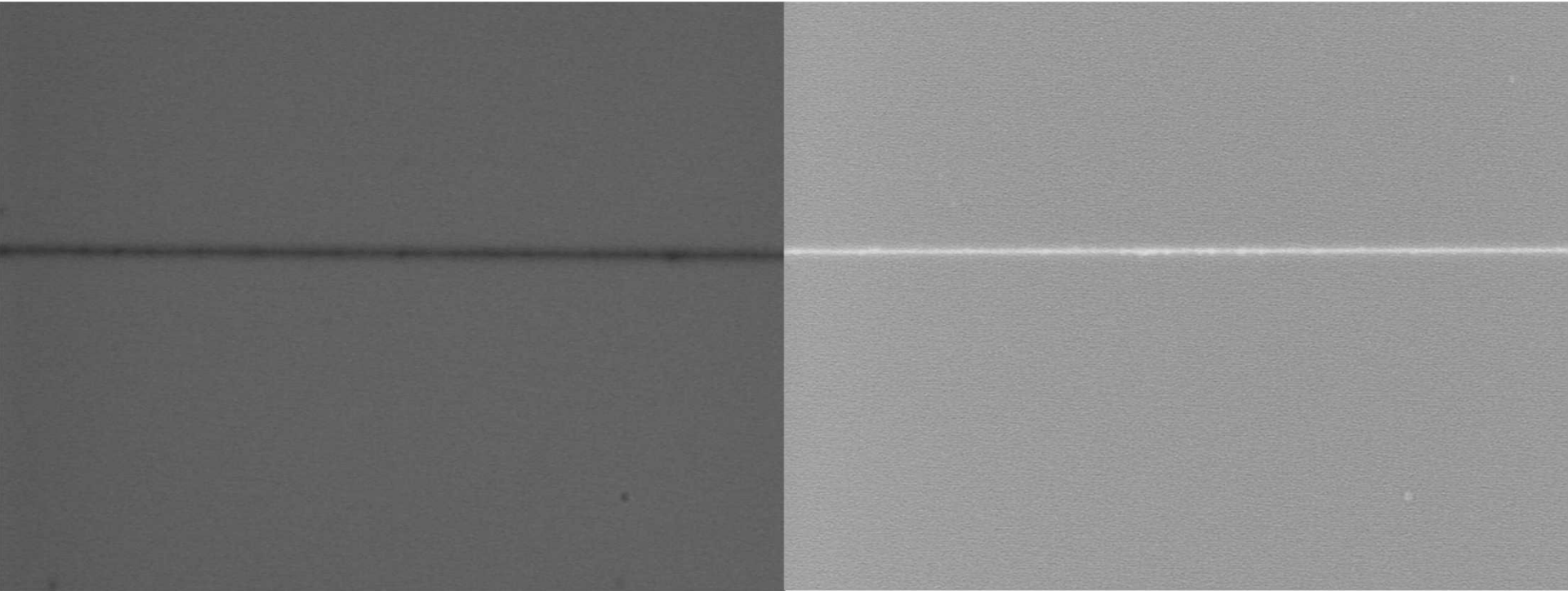


- Typical result
- by non ideal forces during breaking



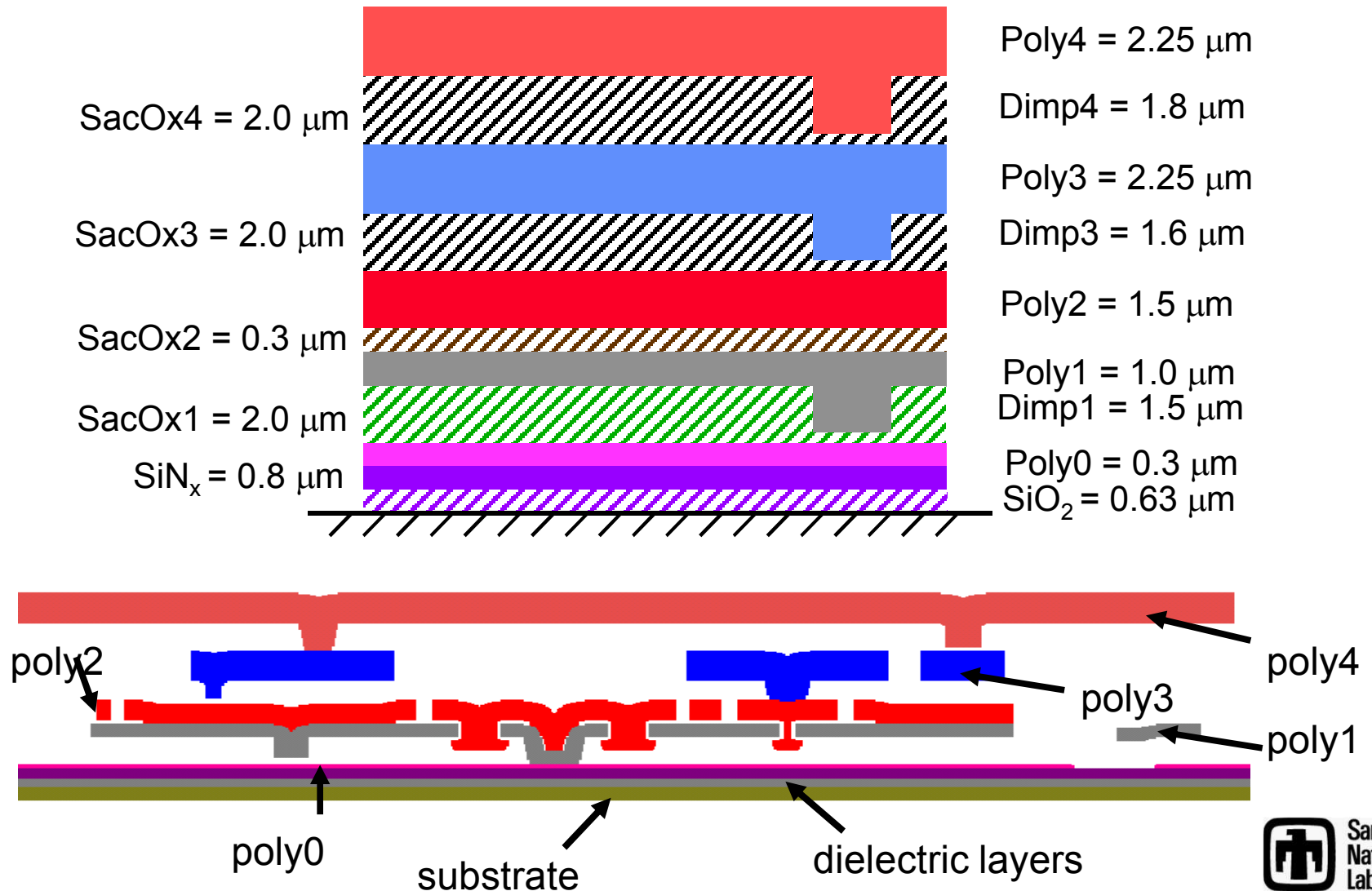
BUT DOES SCRIBING PRODUCE PARTICLES?

- Scribe and break with optimized parameters

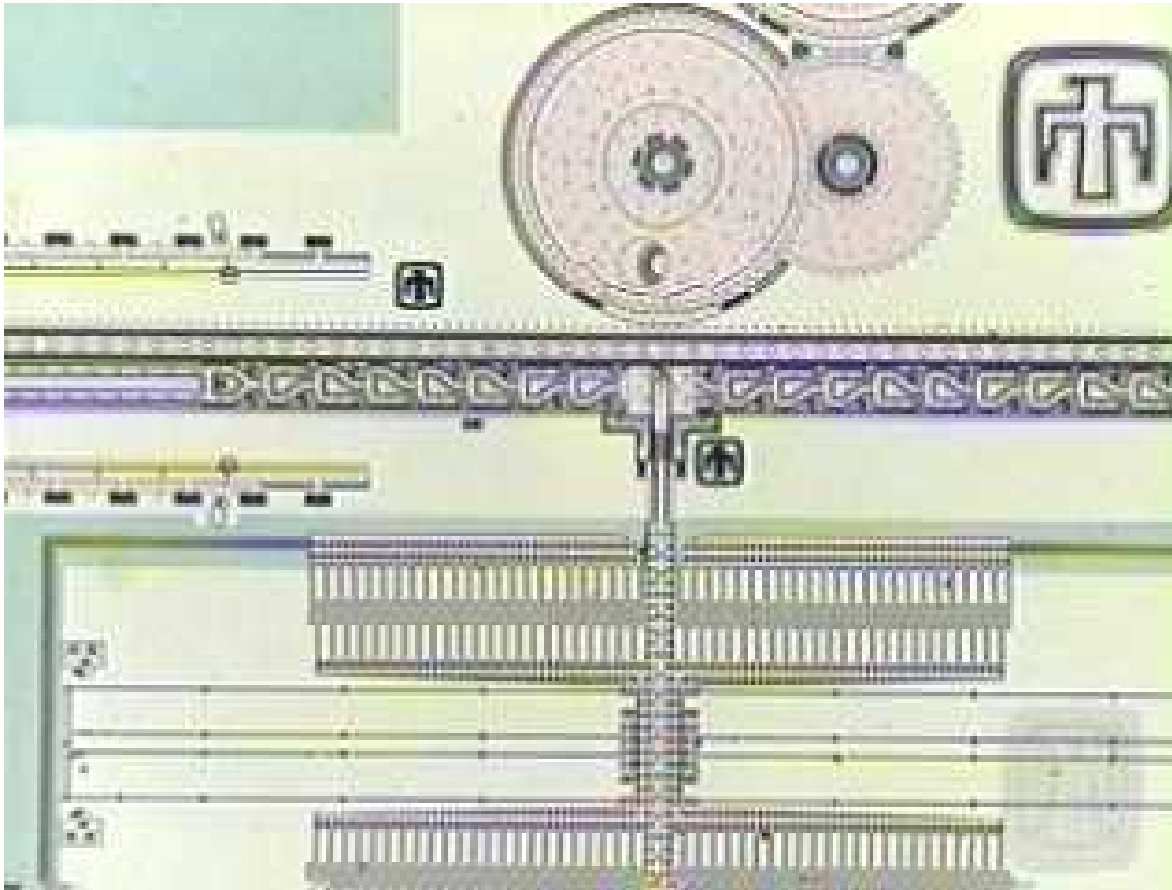


- 2 different scribe lines after break
- Field of view is about 1.1 mm x 1.1 mm

SURFACE MICROMACHINES



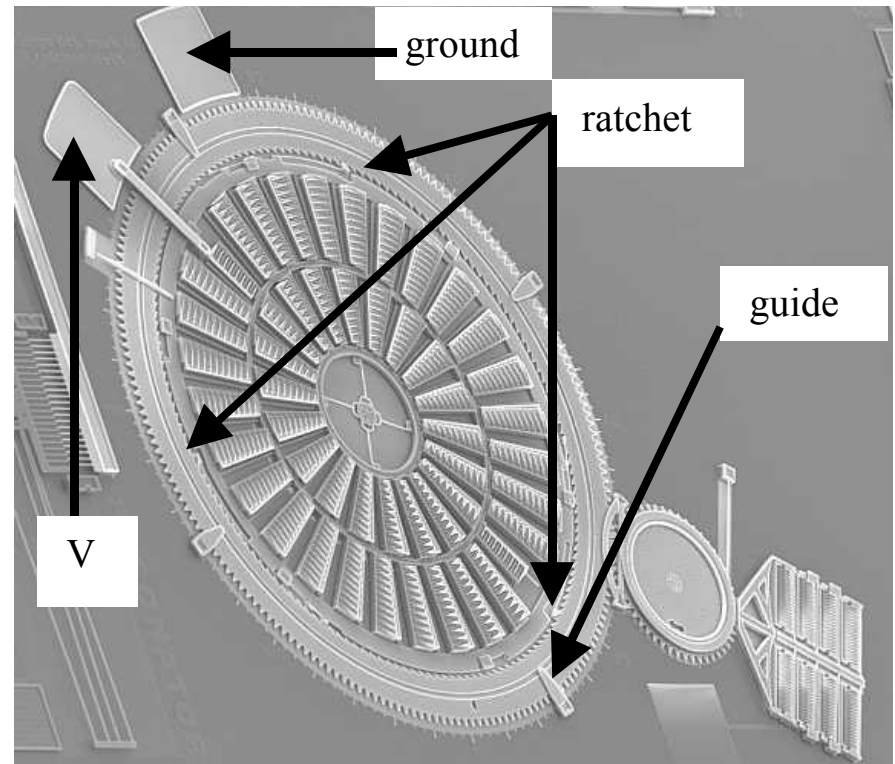
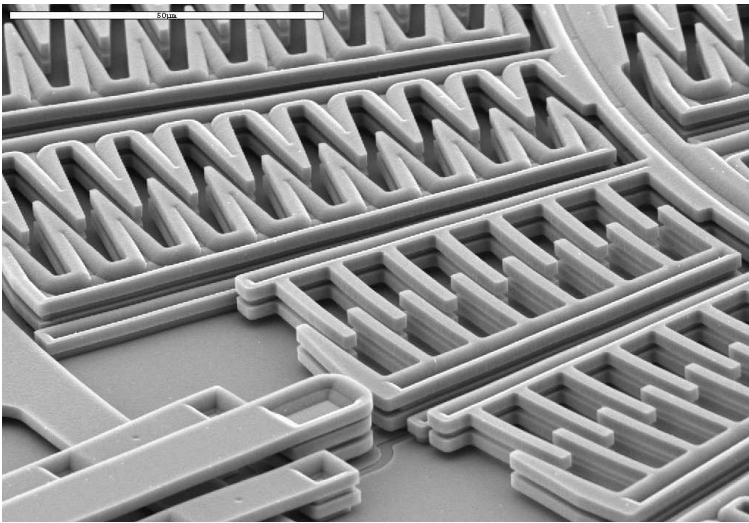
ELECTROSTATIC ACTUATORS



- **Electrostatic actuators tend to attract particles**

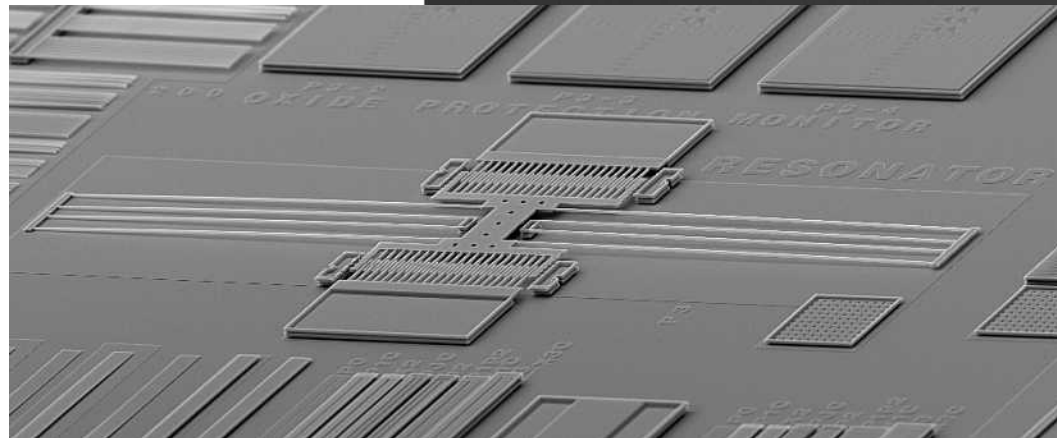
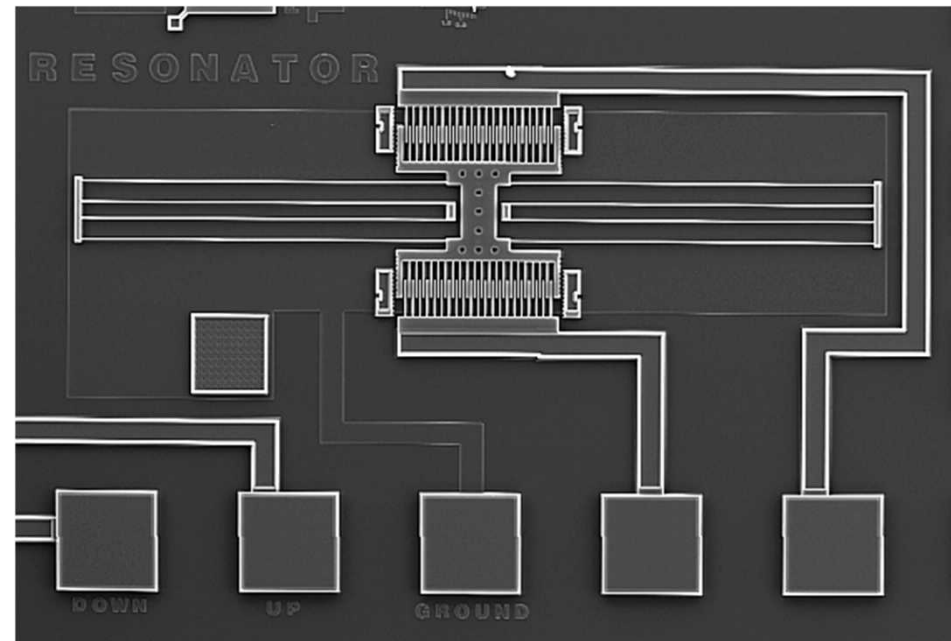
EXPERIMENTAL RESULTS

- **81% Yield on torsional ratcheting actuators (TRA)**



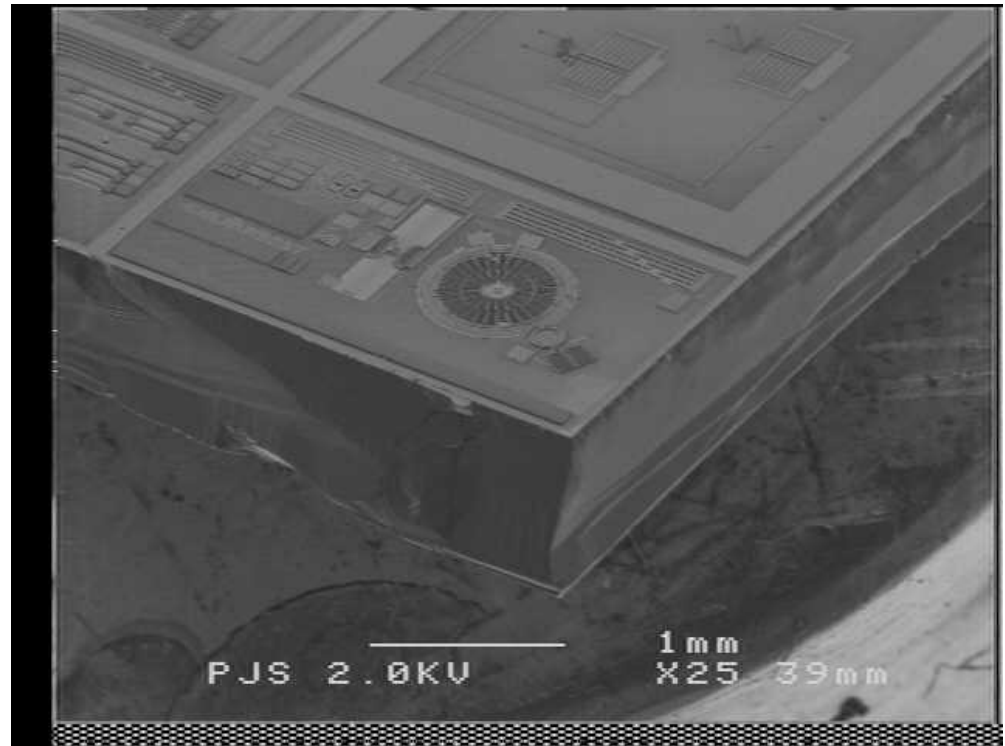
EXPERIMENTAL RESULTS

- 98% yield on resonators

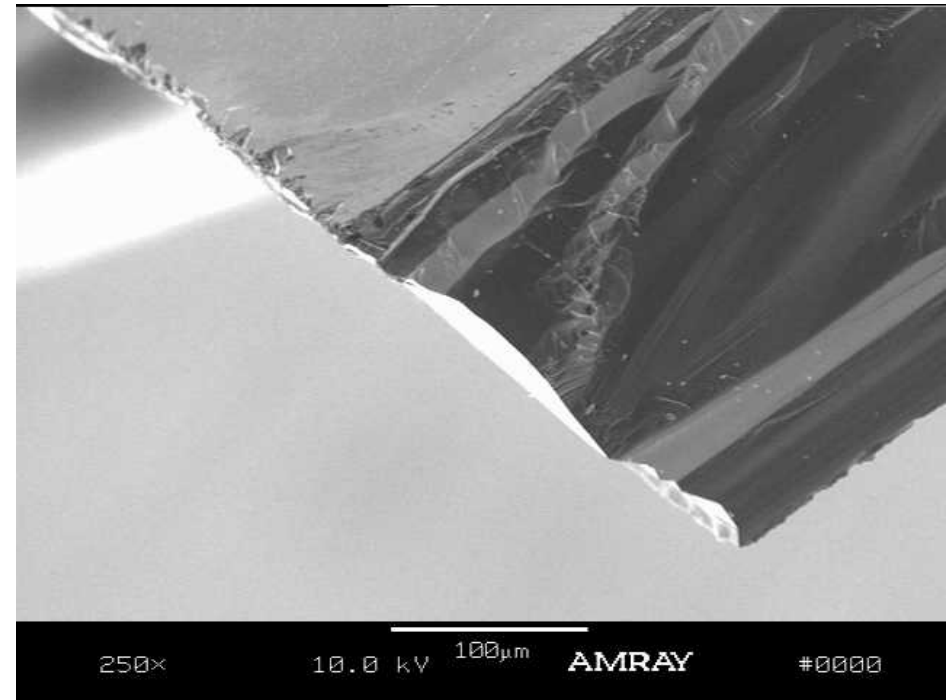
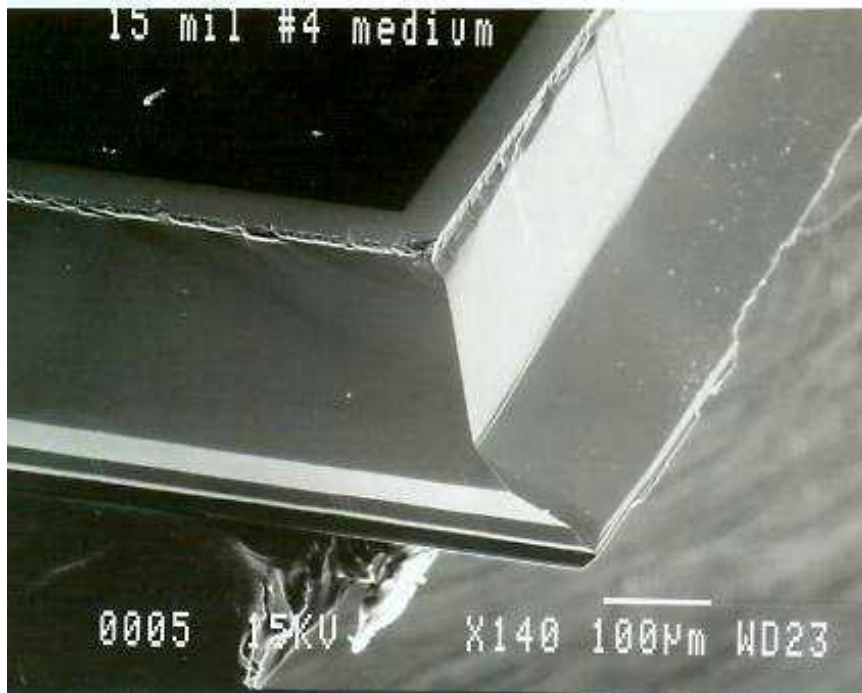


COMPARISONS TO OTHER TECHNIQUES

- Scribe and break is an appropriate and successful technique for enabling full wafer release for SUMMIT™ V.
- However, scribe and break has some limitations
 - The ratio of die size to wafer thickness must be at least 10 to 1
 - Scribe lines must follow the crystal plane
 - Incompatibility with silicon nitride and silicon dioxide and other surface coatings



CANTILEVER CURL



- Mostly caused by non-uniform pressure during the break



CONCLUSIONS

- **Outline**
 - **Why**
 - this approach does work
 - **Yes, we know what is going on**
 - crack depth
 - design of experiments
 - **Yes it works**
 - Micromachines yield after scribe and break
- **Discuss future work**



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